



DTA114T

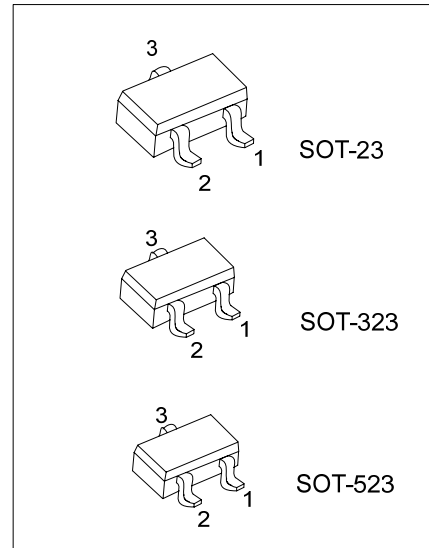
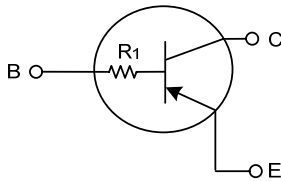
PNP SILICON TRANSISTOR

DIGITAL TRANSISTORS (BUILT-IN BIAS RESISTORS)

FEATURES

- * Built-in bias resistors that implies easy ON/OFF applications.
- * The bias resistors are thin-film resistors with complete isolation to allow positive input.

EQUIVALENT CIRCUIT



*Pb-free plating product number:DTA114TL

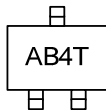
www.DataSheet4U.com

ORDERING INFORMATION

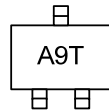
Order Number		Package	Pin Assignment			Packing
Normal	Lead Free Plating		1	2	3	
DTA114T-AE3-R	DTA114TL-AE3-R	SOT-23	E	B	C	Tape Reel
DTA114T-AL3-R	DTA114TL-AL3-R	SOT-323	E	B	C	Tape Reel
DTA114T-AN3-R	DTA114TL-AN3-R	SOT-523	E	B	C	Tape Reel

<p>DTA114TL-AE3-R</p> <p>(1) Packing Type (2) Package Type (3) Lead Plating</p>	<p>(1) R: Tape Reel (2) AE3: SOT-23, AL3: SOT-323, AN3: SOT-523 (3) L: Lead Free Plating, Blank: Pb/Sn</p>
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MARKING



For SOT-23/SOT-323 Package



For SOT-523 Package

■ ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

PARAMETER		SYMBOL	RATING	UNIT
Collector-Base Voltage		V _{CBO}	-50	V
Collector-Emitter Voltage		V _{CEO}	-50	V
Emitter-Base Voltage		V _{EBO}	-5	V
Collector Current		I _C	-100	mA
Collector Power Dissipation	SOT-23	P _C	200	mW
	SOT-323/SOT-523		150	mW
Junction Temperature		T _J	+150	°C
Storage Temperature		T _{STG}	-55~+150	°C

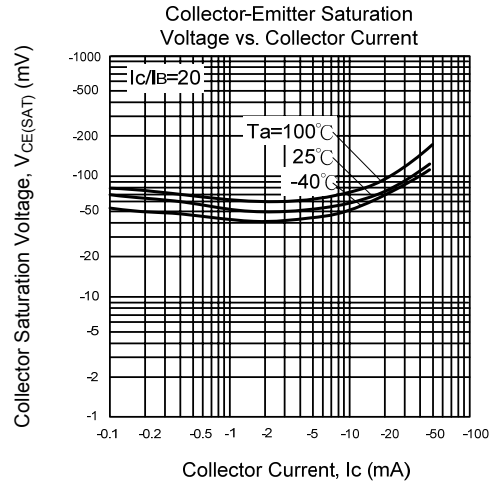
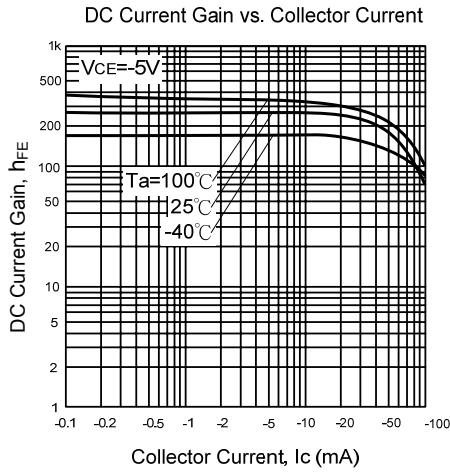
Note Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (Ta= 25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =-50μA	-50			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C =-1mA	-50			V
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E =-50μA	-5			V
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	I _C =-10mA, I _B =-1mA			-0.3	V
Collector Cutoff Current	I _{CBO}	V _{CB} =-50V			-0.5	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} =-4V			-0.5	μA
DC Current Gain	h _{FE}	V _{CE} =-5V, I _C =-1mA	100	250	600	
Input Resistance	R ₁		7	10	13	kΩ
Transition Frequency	f _T	V _{CE} =-10V, I _E =5mA, f=100MHz*		250		MHz

* Transition frequency of the device

■ TYPICAL CHARACTERISTICS



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